











**DRV8839** SLVSBN4B - JANUARY 2013-REVISED DECEMBER 2015

# DRV8839 Low-Voltage Dual ½-H-Bridge Driver IC

#### **Features**

- Dual 1/2-H-Bridge Motor Driver
  - Drives a DC Motor or One Winding of a Stepper Motor, or Other Loads
  - Low MOSFET ON-Resistance:  $HS + LS 280 m\Omega$
- 1.8-A Maximum Drive Current
- Separate Motor and Logic Supply Pins:
  - 0-V to 11-V Motor-Operating Supply-Voltage
  - 1.8-V to 7-V Logic Supply-Voltage
- Separate Motor and Logic Supply Pins
- Individual ½-H-Bridge Control Input Interface
- Low-Power Sleep Mode With 120-nA Maximum Combined Supply Current
- 2.00-mm x 3.00-mm 12-Pin WSON Package

## **Applications**

- Battery-Powered:
  - DSLR Lenses
  - **Consumer Products**
  - Toys
  - Robotics
  - Cameras
  - **Medical Devices**

## 3 Description

The DRV8839 provides a versatile power driver solution for cameras, consumer products, toys, and other low-voltage or battery-powered applications. The device has two independent 1/2-H-bridge drivers and can drive one DC motor or one winding of a stepper motor, as well as other devices like solenoids. The output stages use N-channel power MOSFETs configured as 1/2-H-bridges. An internal charge pump generates needed gate-drive voltages.

The DRV8839 can supply up to 1.8-A of output current. It operates on a motor power supply voltage from 0 V to 11 V and a device power supply voltage of 1.8 V to 7 V.

The DRV8839 has independent input and enable pins for each 1/2-H-bridge which allow independent control of each output.

Internal shutdown functions are provided for protection, overcurrent short-circuit protection, undervoltage lockout, and overtemperature.

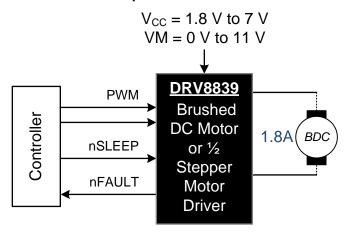
The DRV8839 is packaged in a 12-pin, 2.00-mm × 3.00-mm WSON package (Eco-friendly: RoHS and no Sb/Br).

#### Device Information<sup>(1)</sup>

| PART NUMBER | PACKAGE   | BODY SIZE (NOM)   |  |
|-------------|-----------|-------------------|--|
| DRV8839     | WSON (12) | 2.00 mm × 3.00 mm |  |

(1) For all available packages, see the Orderable Addendum at the end of the datasheet.

#### Simplified Schematic





## **Table of Contents**

| 1 | Features 1                           |    | 7.4 Device Functional Modes                      | g  |
|---|--------------------------------------|----|--|----|
| 2 | Applications 1                       | 8  | Application and Implementation                   | 12 |
| 3 | Description 1                        |    | 8.1 Application Information                      | 12 |
| 4 | Revision History2                    |    | 8.2 Typical Application                          | 12 |
| 5 | Pin Configuration and Functions      | 9  | Power Supply Recommendations                     | 14 |
| 6 | Specifications4                      |    | 9.1 Bulk Capacitance                             | 14 |
| ٠ | 6.1 Absolute Maximum Ratings         | 10 | Layout   | 15 |
|   | 6.2 ESD Ratings                      |    | 10.1 Layout Guidelines                           | 15 |
|   | 6.3 Recommended Operating Conditions |    | 10.2 Layout Example                              | 15 |
|   | 6.4 Thermal Information              |    | 10.3 Thermal Considerations                      | 15 |
|   | 6.5 Electrical Characteristics       | 11 | Device and Documentation Support                 | 17 |
|   | 6.6 Timing Requirements 5            |    | 11.1 Documentation Support                       | 17 |
|   | 6.7 Typical Characteristics          |    | 11.2 Community Resources                         | 17 |
| 7 | Detailed Description 8               |    | 11.3 Trademarks                                  | 17 |
|   | 7.1 Overview 8                       |    | 11.4 Electrostatic Discharge Caution             | 17 |
|   | 7.2 Functional Block Diagram8        |    | 11.5 Glossary                                    | 17 |
|   | 7.3 Feature Description9             | 12 | Mechanical, Packaging, and Orderable Information | 17 |

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

## Changes from Revision A (January 2014) to Revision B

**Page** 

#### Changes from Original (January 2013) to Revision A

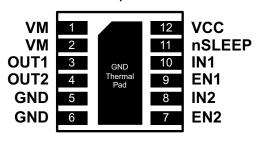
Page

| • | Changed Features bullet  | . 1 |
|---|--|-----|
|   | Changed motor supply voltage range in <i>Description</i> section                             |     |
|   | Changed Motor power supply voltage range in Recommended Operating Conditions                 |     |
|   | Added t <sub>OCR</sub> and t <sub>DEAD</sub> parameters to <i>Electrical Characteristics</i> |     |
| • | Added paragraph to Power Supplies and Input Pins section                                     | 14  |



# 5 Pin Configuration and Functions

DSS Package 12-Pin WSON Top View



#### **Pin Functions**

| F           | NIN      | I/O <sup>(1)</sup> | DESCRIPTION   | EXTERNAL COMPONENTS  |
|-------------|----------|--------------------|---|--|
| NAME NO.    |          | 1/0                | DESCRIPTION   | OR CONNECTIONS   |
| POWER AN    | D GROUND |                    |   |  |
| GND         | 5, 6     |                    | Device ground   |  |
| VCC         | 12       |                    | Device supply   | Bypass to GND with a 0.1-µF, 6.3-V ceramic capacitor   |
| VM          | 1, 2     |                    | Motor supply  | Bypass to GND with a 0.1-µF, 16-V ceramic capacitor  |
| CONTROL     |          |                    | -   |  |
| EN1         | 9        | 1                  | Enable 1 Logic high enables OUT1 Internal pulldown resistor |  |
| EN2         | 7        | 1                  | Enable 2  | Logic high enables OUT2<br>Internal pulldown resistor  |
| IN1         | 10       | 1                  | Input 1   | Logic input controls OUT1<br>Internal pulldown resistor  |
| IN2         | 8        | 1                  | Input 2   | Logic input controls OUT2<br>Internal pulldown resistor  |
| nSLEEP 11 I |          | Ι                  | Sleep mode input  | Logic low puts device in low-power sleep mode<br>Logic high for normal operation<br>Internal pulldown resistor |
| OUTPUT      | •        | •                  | •   |  |
| OUT1        | 3        | 0                  | Output 1  | Connect to motor winding   |
| OUT2        | 4        | 0                  | Output 2  | Connect to motor winding   |
| NO CONNE    | СТ       |                    |   |  |
| NC          | 2, 5     | _                  | No connection   | No connection to these pins  |

<sup>(1)</sup> Directions: I = input, O = output, OZ = tri-state output, OD = open-drain output, IO = input/output.



## 6 Specifications

## 6.1 Absolute Maximum Ratings (1) (2)

Over operating free-air temperature range (unless otherwise noted) (1)

|                  |                                 | MIN       | MAX       | UNIT |
|------------------|---------------------------------|-----------|-----------|------|
|                  | Power supply voltage, VM        | -0.3      | 12        | V    |
|                  | Power supply voltage, VCC       | -0.3      | 7         | V    |
|                  | Digital input pin voltage       | -0.5      | 7         | V    |
|                  | Peak motor drive output current | Internall | y limited | Α    |
| TJ               | Operating junction temperature  | -40       | 150       | °C   |
| T <sub>stg</sub> | Storage temperature             | -60       | 150       | °C   |

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

|                    |                         |  | VALUE | UNIT |
|--------------------|-------------------------|--|-------|------|
|                    |                         | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)                         | ±4000 |      |
| V <sub>(ESD)</sub> | Electrostatic discharge | Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup> | ±1500 | V    |

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

 $T_A = 25$ °C (unless otherwise noted)

|                  |                                  | MIN | NOM MAX | UNIT |
|------------------|----------------------------------|-----|---------|------|
| $V_{CC}$         | Device power supply voltage      | 1.8 | 7       | V    |
| $V_{M}$          | Motor power supply voltage       | 0   | 11      | V    |
| $V_{IN}$         | Logic level input voltage        | 0   | 5.5     | V    |
| I <sub>OUT</sub> | H-bridge output current (1)      | 0   | 1.8     | Α    |
| $f_{PWM}$        | Externally applied PWM frequency | 0   | 250     | kHz  |

<sup>(1)</sup> Power dissipation and thermal limits must be observed.

### 6.4 Thermal Information

|                        |  | DRV8839    |      |
|------------------------|--|------------|------|
|                        | THERMAL METRIC <sup>(1)</sup>                | DSS (WSON) | UNIT |
|                        |  | 12 PINS    |      |
| $R_{\theta JA}$        | Junction-to-ambient thermal resistance       | 50.4       | °C/W |
| $R_{\theta JC(top)}$   | Junction-to-case (top) thermal resistance    | 58         | °C/W |
| $R_{\theta JB}$        | Junction-to-board thermal resistance         | 19.9       | °C/W |
| ΨЈΤ                    | Junction-to-top characterization parameter   | 0.9        | °C/W |
| ΨЈВ                    | Junction-to-board characterization parameter | 20         | °C/W |
| R <sub>0</sub> JC(bot) | Junction-to-case (bottom) thermal resistance | 6.9        | °C/W |

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

<sup>(2)</sup> All voltage values are with respect to network ground terminal.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.5 Electrical Characteristics

 $T_A = 25$ °C,  $V_M = 5$  V,  $V_{CC} = 3$  V (unless otherwise noted)

|                        | PARAMETER                         | TEST CONDITIONS                                | MIN                    | TYP                    | MAX                    | UNIT |  |
|------------------------|-----------------------------------|--|------------------------|------------------------|------------------------|------|--|
| POWER S                | SUPPLY                            |  |                        |                        |                        |      |  |
|                        | V/M                               | No PWM   |                        | 40                     | 100                    | μA   |  |
| $I_{VM}$               | VM operating supply current       | 50 kHz PWM                                     |                        | 0.8                    | 1.5                    | mA   |  |
| I <sub>VMQ</sub>       | VM sleep mode supply current      | nSLEEP = 0 V                                   |                        | 30                     | 95                     | nA   |  |
|                        | VCCti                             | No PWM   |                        | 300                    | 500                    | μA   |  |
| VCC clear made current |                                   | 50 kHz PWM                                     |                        | 0.7                    | 1.5                    | mA   |  |
| I <sub>VCCQ</sub>      | VCC sleep mode supply current     | nSLEEP = 0 V                                   |                        | 5                      | 25                     | nA   |  |
| .,                     | VCC undervoltage lockout          | V <sub>CC</sub> rising                         |                        |                        | 1.8                    |      |  |
| $V_{UVLO}$             | voltage                           | V <sub>CC</sub> falling                        |                        |                        | 1.7                    | V    |  |
| LOGIC-LI               | EVEL INPUTS                       |  |                        |                        |                        |      |  |
| V <sub>IL</sub>        | Input low voltage                 |  | 0.31 × V <sub>CC</sub> | 0.34 × V <sub>CC</sub> |                        | V    |  |
| V <sub>IH</sub>        | Input high voltage                |  |                        | 0.39 × V <sub>CC</sub> | 0.43 × V <sub>CC</sub> | V    |  |
| V <sub>HYS</sub>       | Input hysteresis                  |  |                        | 0.08 × V <sub>CC</sub> |                        | V    |  |
| I <sub>IL</sub>        | Input low current                 | V <sub>IN</sub> = 0                            | -5                     |                        | 5                      | μA   |  |
| I <sub>IH</sub>        | Input high current                | V <sub>IN</sub> = 3.3 V                        |                        |                        | 50                     | μA   |  |
| R <sub>PD</sub>        | Pulldown resistance               |  |                        | 100                    |                        | kΩ   |  |
| H-BRIDG                | E FETS                            |  | •                      |                        |                        |      |  |
| R <sub>DS(ON)</sub>    | HS + LS FET on resistance         | I <sub>O</sub> = 800 mA, T <sub>J</sub> = 25°C |                        | 280                    | 330                    | mΩ   |  |
| I <sub>OFF</sub>       | OFF-state leakage current         |  |                        |                        | ±200                   | nA   |  |
| PROTEC                 | TION CIRCUITS                     |  |                        |                        | <u> </u>               |      |  |
| I <sub>OCP</sub>       | Overcurrent protection trip level |  | 1.9                    |                        | 3.5                    | Α    |  |
| t <sub>OCR</sub>       | Overcurrent protection retry time |  |                        | 1                      |                        | ms   |  |
| t <sub>DEAD</sub>      | Output dead time                  |  |                        | 100                    |                        | ns   |  |
| t <sub>TSD</sub>       | Thermal shutdown temperature      | Die temperature                                | 150                    | 160                    | 180                    | °C   |  |

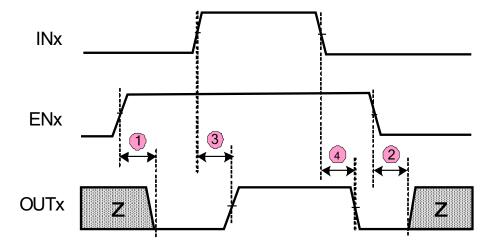
## 6.6 Timing Requirements (1)

 $T_A = 25^{\circ}C$ ,  $V_M = 5$  V,  $V_{CC} = 3$  V,  $R_L = 20$   $\Omega$ 

|   |                |                                   | MIN | MAX | UNIT |
|---|----------------|-----------------------------------|-----|-----|------|
| 1 | t <sub>1</sub> | Output enable time                |     | 120 | ns   |
| 2 | t <sub>2</sub> | Output disable time               |     | 120 | ns   |
| 3 | t <sub>3</sub> | Delay time, INx high to OUTx high |     | 120 | ns   |
| 4 | t <sub>4</sub> | Delay time, INx low to OUTx low   |     | 120 | ns   |
| 5 | t <sub>5</sub> | Output rise time                  | 50  | 150 | ns   |
| 6 | t <sub>6</sub> | Output fall time                  | 50  | 150 | ns   |

(1) Not production tested – ensured by design





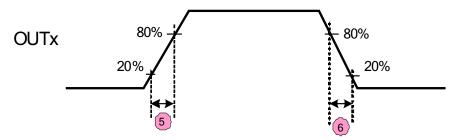
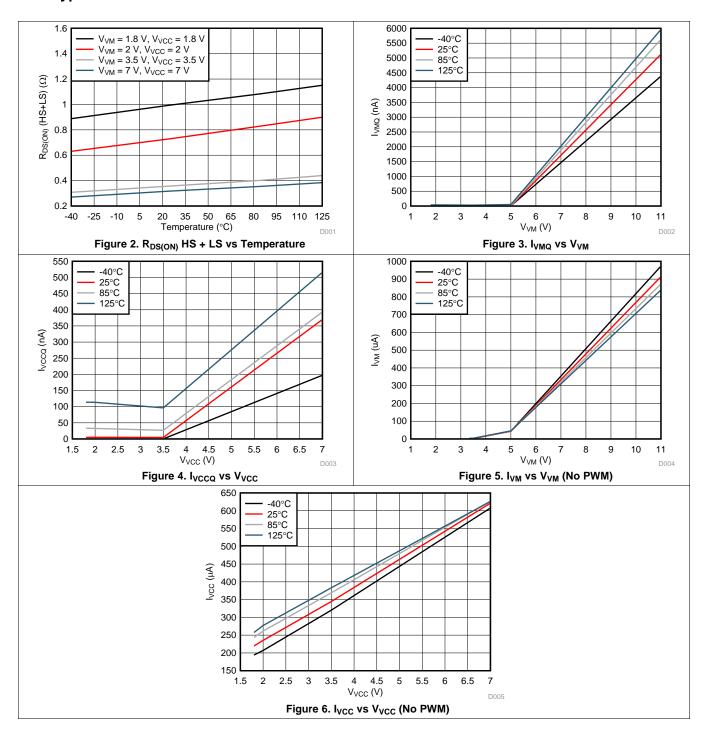


Figure 1. Timing Requirements

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## 6.7 Typical Characteristics





## 7 Detailed Description

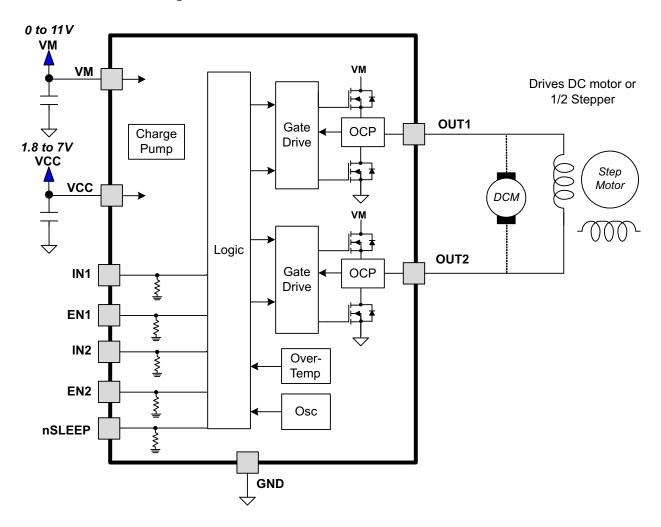
#### 7.1 Overview

The DRV8839 is an integrated motor driver solution used for brushed motor control. The device integrates two independent ½ H-bridge, and can drive one motor in both directions or two motors in one direction. The output driver block for each ½ H-bridge consists of N-channel power MOSFETs. An internal charge pump generates the gate drive voltages. Protection features include overcurrent protection, short-circuit protection, undervoltage lockout, and overtemperature protection.

The DRV8839 allows separation of the motor voltage and logic voltage if desired. If VM and VCC are less than 7 V, the two voltages may be connected.

The control interface of the DRV8839 uses INx and ENx to control each ½ H-bridge separately.

## 7.2 Functional Block Diagram





## 7.3 Feature Description

#### 7.3.1 Protection Circuits

The DRV8839 is fully protected against undervoltage, overcurrent, and overtemperature events.

#### 7.3.1.1 Overcurrent Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP time, all FETs in the H-bridge disables. After approximately 1 ms, the bridge will be re-enabled automatically.

Overcurrent conditions on both high-side and low-side devices; a short to ground, supply, or across the motor winding result in an overcurrent shutdown.

#### 7.3.1.2 Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge disables. Operation automatically resumes once the die temperature has fallen to a safe level.

#### 7.3.1.3 Undervoltage Lockout (UVLO)

If at any time the voltage on the VCC pin falls below the undervoltage lockout threshold voltage, all circuitry in the device disables and internal logic resets. Operation resumes when VCC rises above the UVLO threshold.

**Table 1. Device Protection** 

| FAULT                   | CONDITION   | ERROR REPORT | H-BRIDGE | INTERNAL<br>CIRCUITS | RECOVERY         |
|-------------------------|-------------|--------------|----------|----------------------|------------------|
| VCC undervoltage (UVLO) | VCC < VUVLO | None         | Disabled | Disabled             | VCC > VUVLO      |
| Overcurrent (OCP)       | IOUT > IOCP | None         | Disabled | Operating            | tOCR             |
| Thermal shutdown (TSD)  | TJ > TTSD   | None         | Disabled | Operating            | TJ < TTSD - THYS |

#### 7.4 Device Functional Modes

The DRV8839 is active when the nSLEEP pin is set to a logic high. When in sleep mode, the ½ H-bridge FETs are disabled (High-Z).

**Table 2. Device Operating Modes** 

| OPERATING MODE    | CONDITION               | H-BRIDGE  | INTERNAL CIRCUITS |
|-------------------|-------------------------|-----------|-------------------|
| Operating         | nSLEEP high             | Operating | Operating         |
| Sleep mode        | nSLEEP low              | Disabled  | Disabled          |
| Fault encountered | Any fault condition met | Disabled  | See Table 1       |

## 7.4.1 Bridge Control

The DRV8839 is controlled using separate enable and input pins for each ½-H-bridge.

The following table shows the logic for the DRV8839:

**Table 3. Bridge Control** 

| ENx | INx | OUTx |
|-----|-----|------|
| 0   | X   | Z    |
| 1   | 0   | L    |
| 1   | 1   | Н    |



## 7.4.2 Sleep Mode

If the nSLEEP pin reaches a logic-low state, the DRV8839 enters a low-power sleep mode. In this state all unnecessary internal circuitry powers down.

#### 7.4.3 Motor Connections

If a single DC motor connects to the DRV8839, it is connected between the OUT1 and OUT2 pins as shown in Figure 7:

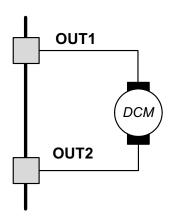


Figure 7. Single DC Motor Connection

Motor operation is controlled as follows:

**Table 4. Single DC Motor Operation** 

| EN1 | EN2 | IN1 | IN2 | OUT1                   | OUT2 | MOTOR OPERATION |
|-----|-----|-----|-----|------------------------|------|-----------------|
| 0   | X   | X   | X   | X Z See <sup>(1)</sup> |      | Off (coast)     |
| X   | 0   | X   | X   | See (2)                | Z    | Off (coast)     |
| 1   | 1   | 0   | 0   | L                      | L    | Brake           |
| 1   | 1   | 0   | 1   | L                      | Н    | Reverse         |
| 1   | 1   | 1   | 0   | Н                      | L    | Forward         |
| 1   | 1   | 1   | 1   | Н                      | Н    | Brake           |

- (1) State depends on EN2 and IN2, but does not affect motor operation because OUT1 is tri-stated.
- (2) State depends on EN1 and IN1, but does not affect motor operation because OUT2 is tri-stated.



Two DC motors can be connected to the DRV8839. In this mode, it is not possible to reverse the direction of the motors; they turn only in one direction. The connections are shown in Figure 8:

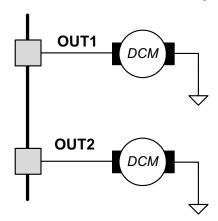


Figure 8. Dual DC Motor Connection

Motor operation is controlled as follows:

**Table 5. Dual DC Motor Operation** 

| ENx | INx | OUTx | MOTOR OPERATION |
|-----|-----|------|-----------------|
| 0   | X   | Z    | Off (coast)     |
| 1   | 0   | L    | Brake           |
| 1   | 1   | Н    | Forward         |



## 8 Application and Implementation

#### **NOTE**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 8.1 Application Information

The DRV8839 is used in one control applications.

## 8.2 Typical Application

The following design is a common application of the DRV8839.

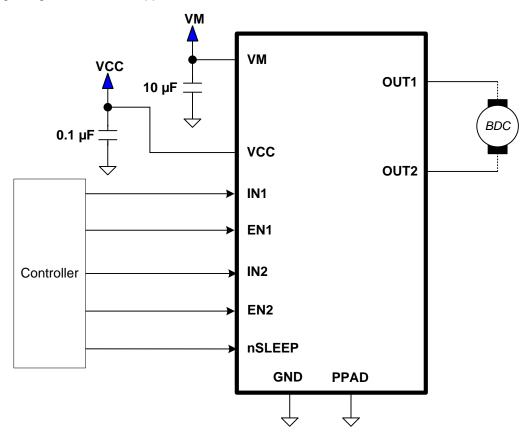


Figure 9. Typical Application Schematic

#### 8.2.1 Design Requirements

The design requirements are shown in Table 6.

**Table 6. Design Requirements** 

| DESIGN PARAMETER      | REFERENCE | EXAMPLE VALUE |  |  |  |
|-----------------------|-----------|---------------|--|--|--|
| Motor voltage         | VM        | 5 V           |  |  |  |
| Motor RMS current     | IRMS      | 0.3 A         |  |  |  |
| Motor startup current | ISTART    | 0.6 A         |  |  |  |



#### 8.2.2 Detailed Design Procedure

The following design procedure can be used to configure the DRV8839 in a brushed motor application.

## 8.2.2.1 Motor Voltage

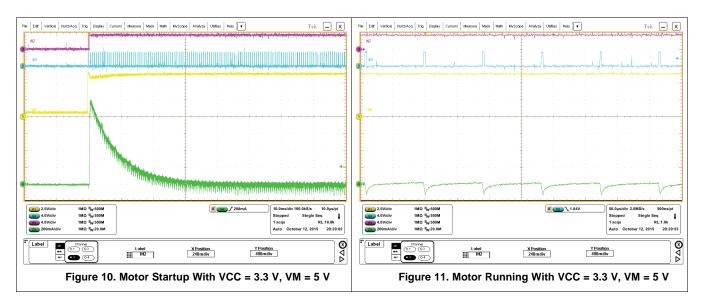
The appropriate motor voltage depends on the ratings of the motor selected and the desired RPM. A higher voltage spins a brushed DC motor faster with the same PWM duty cycle applied to the power FETs. A higher voltage also increases the rate of current change through the inductive motor windings.

#### 8.2.2.2 Low-Power Operation

When entering sleep mode, TI recommends setting all inputs as a logic low to minimize system power.

#### 8.2.2.3 Application Curves

The following scope captures show a typical motor startup and running. Channel 1 is VM, Channel 2 is IN1, Channel 3 is IN2, and Channel 4 is motor current. the motor used is a NMB Technologies, PPN7PA12C1.





## 9 Power Supply Recommendations

The input pins can drive within their recommended operating conditions with or without the VCC and VM power supplies present. No leakage current path exists to the supply. There is a weak pulldown resistor (approximately  $100 \text{ k}\Omega$ ) to ground on each input pin.

VCC and VM can be applied and removed in any order. When VCC is removed, the device enters a low-power state and draws very little current from VM. If the supply voltage is between 1.8 V and 7 V, VCC and VM can connect together.

The VM voltage supply does not have any undervoltage lockout protection (UVLO), so as long as VCC > 1.8 V, the internal device logic remains active. This means that the VM pin voltage may drop to 0 V, however, the load may not be sufficiently driven at low VM voltages.

## 9.1 Bulk Capacitance

Having appropriate local bulk capacitance is an important factor in motor drive system design. It is generally beneficial to have more bulk capacitance, while the disadvantages are increased cost and physical size.

The required amount of local capacitance depends on a variety of factors, including:

- · The highest current required by the motor system
- The power supply's capacitance and ability to source current
- · The amount of parasitic inductance between the power supply and motor system
- The acceptable voltage ripple
- The type of motor used (brushed DC, brushless DC, stepper)
- · The motor braking method

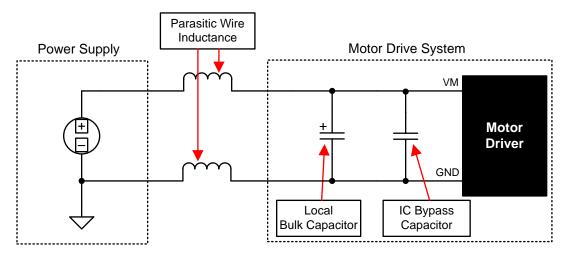


Figure 12. Bulk Capacitance



## 10 Layout

## 10.1 Layout Guidelines

The VCC pin should be bypassed to GND using low-ESR ceramic bypass capacitors with a recommended value of 0.1- $\mu$ F rated for VCC. This capacitor should be placed as close to the VCC pin as possible with a thick trace or ground plane connection to the device GND pin.

The VCC pin must be bypassed to ground using an appropriate bulk capacitor. This component may be an electrolytic and should be located close to the DRV8839.

## 10.2 Layout Example

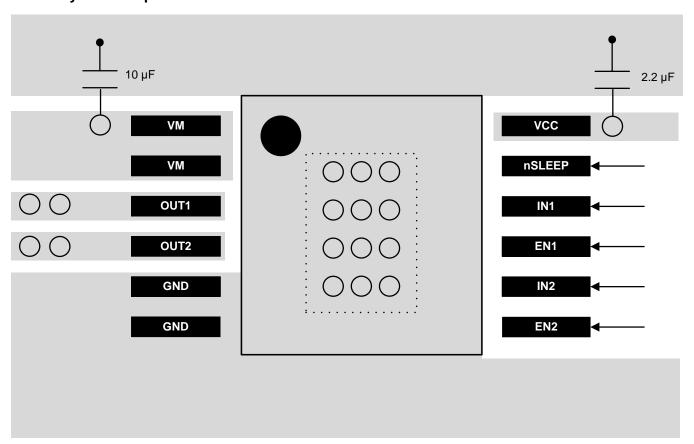


Figure 13. Layout Recommendation

#### 10.3 Thermal Considerations

The DRV8839 has thermal shutdown (TSD) as described above. If the die temperature exceeds approximately 150°C, the device disables until the temperature drops to a safe level.

Any tendency of the device to enter thermal shutdown is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

#### 10.3.1 Power Dissipation

The power dissipation of the DRV8839 is a function of RMS motor current and the each output's FET resistance  $(R_{DS(ON)})$  as seen in Equation 1:

Power 
$$\approx I_{RMS}^2 \times (High-Side R_{DS(ON)} + Low-Side R_{DS(ON)})$$
 (1)



## Thermal Considerations (continued)

For this example,  $V_{VM}$  = 1.8 V,  $V_{VCC}$  = 1.8 V, the ambient temperature is 35°C, and the junction temperature reaches 65°C. At 65°C, the sum of  $R_{DS(ON)}$  is about 1  $\Omega$ . With an example motor current of 0.8 A, the dissipated power in the form of heat will be 0.8 A² × 1  $\Omega$  = 0.64 W.

The temperature that the DRV8839 reaches will depend on the thermal resistance to the air and PCB. It is important to solder the device PowerPAD to the PCB ground plane, with vias to the top and bottom board layers, in order dissipate heat into the PCB and reduce the device temperature. In the example used here, the DRV8839 had an effective thermal resistance  $R_{\theta,JA}$  of 47°C/W, and as seen in Equation 2:

$$T_J = T_A + (P_D \times R_{\theta JA}) = 35^{\circ}C + (0.64 \text{ W} \times 47^{\circ}C/\text{W}) = 65^{\circ}C$$
 (2)



## 11 Device and Documentation Support

## 11.1 Documentation Support

#### 11.1.1 Related Documentation

For related documentation see the following:

- PowerPAD™ Thermally Enhanced Package Application report SLMA002
- PowerPAD™ Made Easy SLMA004

## 11.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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#### 11.3 Trademarks

PowerPAD, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

#### 11.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 11.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGE OPTION ADDENDUM

28-Oct-2014

#### PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package<br>Drawing | Pins | Package<br>Qty | Eco Plan                   | Lead/Ball Finish | MSL Peak Temp       | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|----------------------------|------------------|---------------------|--------------|----------------------|---------|
| DRV8839DSSR      | ACTIVE | WSON         | DSS                | 12   | 3000           | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-2-260C-1 YEAR | -40 to 85    | 8839                 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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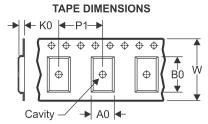
28-Oct-2014

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 28-Oct-2014

## TAPE AND REEL INFORMATION





|    | Dimension designed to accommodate the component width     |
|----|---|
| В0 | Dimension designed to accommodate the component length    |
| K0 | Dimension designed to accommodate the component thickness |
| W  | Overall width of the carrier tape                         |
| P1 | Pitch between successive cavity centers                   |

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

| Device      | Package<br>Type | Package<br>Drawing |    |      | Reel<br>Diameter<br>(mm) | Reel<br>Width<br>W1 (mm) | A0<br>(mm) | B0<br>(mm) | K0<br>(mm) | P1<br>(mm) | W<br>(mm) | Pin1<br>Quadrant |
|-------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| DRV8839DSSR | WSON            | DSS                | 12 | 3000 | 180.0                    | 8.4                      | 2.25       | 3.25       | 1.05       | 4.0        | 8.0       | Q1               |

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 28-Oct-2014

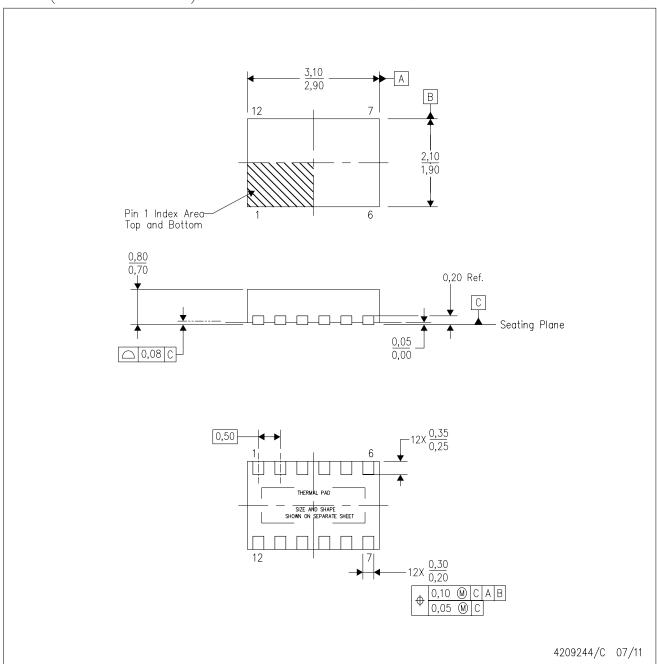


#### \*All dimensions are nominal

| Device   |     | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|----------|-----|--------------|-----------------|------|------|-------------|------------|-------------|
| DRV8839D | SSR | WSON         | DSS             | 12   | 3000 | 210.0       | 185.0      | 35.0        |

DSS (R-PWSON-N12)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. SON (Small Outline No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.



## DSS (R-PWSON-N12)

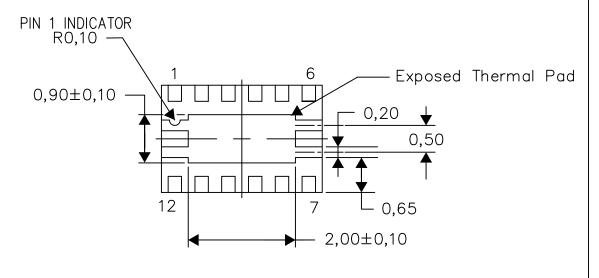
PLASTIC SMALL OUTLINE NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

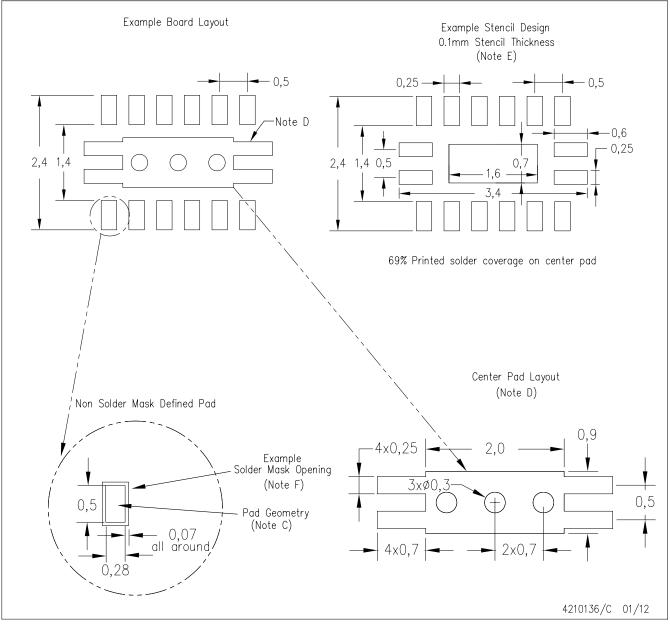
4210135-2/D 02/16

NOTE: All linear dimensions are in millimeters



# DSS (R-PWSON-N12)

## PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for solder mask tolerances.



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